

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

1-15. (Canceled)

16. (Previously Presented) An active matrix circuit comprising:
a semiconductor layer;
a p-type impurity region provided in said semiconductor layer;
a first interlayer insulating film comprising silicon nitride provided over said semiconductor layer;
a conductive layer comprising titanium and aluminum over said first interlayer insulating film; and
a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor layer,
wherein said titanium and said aluminum are formed in a multi-layer film.
17. (Previously Presented): A circuit according to claim 16 wherein said active matrix circuit is incorporated into a liquid-crystal display.
18. (Previously Presented): A circuit according to claim 16 wherein said active matrix circuit is incorporated into an image sensor.
19. (Previously Presented): A circuit according to claim 16 wherein said active matrix circuit is incorporated into a liquid-crystal electro-optical device.
20. (Previously Presented): A circuit according to claim 16 wherein said semiconductor layer comprises a crystal silicon.

21. (Previously Presented): An active matrix circuit comprising:
a semiconductor layer;
a p-type impurity region provided in said semiconductor layer;
a first interlayer insulating film comprising a silicon nitride layer and a silicon oxide layer, said first interlayer insulating film provided over said semiconductor layer;
a conductive layer comprising titanium and aluminum over said first interlayer insulating film; and
a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor layer.

22. (Previously Presented): A circuit according to claim 21 wherein said active matrix circuit is incorporated into a liquid-crystal display.

23. (Previously Presented): A circuit according to claim 21 wherein said active matrix circuit is incorporated into an image sensor.

24. (Previously Presented): A circuit according to claim 21 wherein said active matrix circuit is incorporated into a liquid-crystal electro-optical device

25. (Previously Presented): A circuit according to claim 21 wherein said semiconductor layer comprises a crystal silicon.

26. (Previously Presented): An active matrix circuit comprising:
a semiconductor layer;
a p-type impurity region provided in said semiconductor layer;
a first interlayer insulating film comprising silicon nitride provided over said semiconductor layer;

a conductive layer comprising titanium and aluminum over said first interlayer insulating film; and

a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor layer.

27. (Previously Presented): A circuit according to claim 26 wherein said conductive layer comprises an electrode.

28. (Previously Presented): A circuit according to claim 26 wherein said conductive layer comprises a wiring.

29. (Previously Presented): A circuit according to claim 26 wherein said active matrix circuit is incorporated into a liquid-crystal display.

30. (Previously Presented): A circuit according to claim 26 wherein said active matrix circuit is incorporated into an image sensor.

31. (Previously Presented): A circuit according to claim 26 wherein said active matrix circuit is incorporated into a liquid-crystal electro-optical device.

32. (Previously Presented): A circuit according to claim 26 wherein said semiconductor layer comprises a crystal silicon.

33. (Canceled).

34. (New): An active matrix circuit comprising:

a semiconductor layer;

a p-type impurity region provided in said semiconductor layer;

a first interlayer insulating film comprising silicon nitride provided over said semiconductor layer;

a conductive layer comprising titanium and aluminum over said first interlayer insulating film, said conductive layer connected with said p-type impurity region; and

a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor layer,
wherein said titanium and said aluminum are formed in a multi-layer film.

35. (New): A circuit according to claim 34 wherein said active matrix circuit is incorporated into a liquid-crystal display.

36. (New): A circuit according to claim 34 wherein said active matrix circuit is incorporated into an image sensor.

37. (New): A circuit according to claim 34 wherein said semiconductor layer comprises a crystal silicon.

38. (New): An active matrix circuit comprising:

a semiconductor layer;

a p-type impurity region provided in said semiconductor layer;

a first interlayer insulating film comprising a silicon nitride layer and a silicon oxide layer, said first interlayer insulating film provided over said semiconductor layer;

a conductive layer comprising titanium and aluminum over said first interlayer insulating film, said conductive layer connected with said p-type impurity region; and

a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor layer.

39. (New): A circuit according to claim 38 wherein said active matrix circuit is incorporated into a liquid-crystal display.

40. (New): A circuit according to claim 38 wherein said active matrix circuit is incorporated into an image sensor.

41. (New): A circuit according to claim 38 wherein said semiconductor layer comprises a crystal silicon.

42. (New): An active matrix circuit comprising:
a semiconductor layer;
a p-type impurity region provided in said semiconductor layer;
a first interlayer insulating film comprising silicon nitride provided over said semiconductor layer;
a conductive layer comprising titanium and aluminum over said first interlayer insulating film, said conductive layer connected with said p-type impurity region; and
a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor layer.

43. (New): A circuit according to claim 42 wherein said active matrix circuit is incorporated into a liquid-crystal display.

44. (New): A circuit according to claim 42 wherein said active matrix circuit is incorporated into an image sensor.

45. (New): A circuit according to claim 42 wherein said semiconductor layer comprises a crystal silicon.